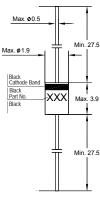
SILICON BIDIRECTIONAL DIACS

The glass passivated, three-layer, two terminal, axial lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current. The breakover symmetry is within four volts with a typical breakover voltage of DB-3 32 V, DB-4 40 V. These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.

Storage Temperature Range T_S - 40 °C to +150 °C Operating Temperature Range T_J - 40 °C to +100 °C



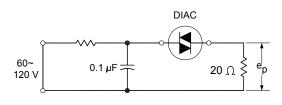
Glass Case DO-35 Dimensions in mm

MAXIMUM RATINGS at 50 °C Ambient

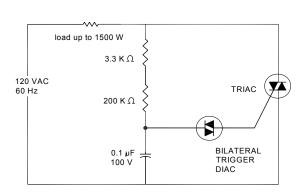
Peak Current (10 μ s duration, 120 cycle repetition rate) I_P ± 2 A Max. Peak output voltage e_P 3 ± Volts Max.¹⁾

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
Breakover Voltage	DB-3	V _{(BR)1} and V _{(BR)2}	28	36	V
	DB-4		35	45	
Breakover Currents		$I_{(BR)1}$ and $I_{(BR)2}$	-	200	μΑ
Breakover Voltage Symmetry		[V _{(BR)1}]-[V _{(BR)2}]	-	3.8	V
Dynamic Breakover Voltage $\Delta I = [I_{BR} \text{ to } I_{F} = 10 \text{ mA}]$		ΔV ±	5	-	V
Thermal Impedance Junction to Ambient Air		R _{eJA}	-	60	°C/W



¹⁾ CIRCUIT FOR PEAK OUTPUT VOLTAGE TEST



TYPICAL DIAC-TRIAC FULL-WAVE PHASE CONTROL CIRCUIT